ST 2SA608N

PNP Silicon Epitaxial Planar Transistor

Low - Frequency General - Purpose Amplifier Applications.

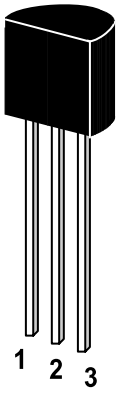
The transistor is subdivided into two groups F and G according to its DC current gain.

Applications:

- Capable of being used in the low frequency to high frequency range.

Features:

- Large current capacity and wide ASO.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	150	mA
Collector Current (Pulse)	$-I_{CP}$	400	mA
Collector Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	^OC
Storage Temperature Range	T_S	-55 to +150	^OC

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Characteristics at T_{amb}=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE}$=6V, $-I_C$=1mA					
Current Gain Group F	h_{FE}	160	-	320	-
G	h_{FE}	280	-	560	-
at $-V_{CE}$=6V, $-I_C$=0.1mA	h_{FE}	70	-	-	-
Collector Base Breakdown Voltage					
at $-I_C$=10μA	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage					
at $-I_C$=1mA	$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage					
at $-I_E$=10μA	$-V_{(BR)EBO}$	6	-	-	V
Collector Cutoff Current					
at $-V_{CB}$=40V	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current					
at $-V_{EB}$=5V	$-I_{EBO}$	-	-	0.1	μA
Collector Emitter Saturation Voltage					
at $-I_C$=100mA, $-I_B$=10mA	$-V_{CE(sat)}$	-	-	0.3	V
Base Emitter Saturation Voltage					
at $-I_C$=100mA, $-I_B$=10mA	$-V_{BE(sat)}$	-	-	1	V
Gain Bandwidth Product					
at $-V_{CE}$=6V, $-I_C$=10mA	f_T	-	200	-	MHz
Output Capacitance					
at $-V_{CB}$=6V, f=1MHz	C_{OB}	-	4.5	-	pF